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Introduction to Cycle Time Management Part 1

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Acknowledgements: Motorola's Cycle Time Reduction Team, Jack Scholl, Michael Mandracchia, Jerry Walton, Jerry Chruma, Virgil Howarth, Gene Mullinnix, Michael Wolfe, Tom Filesi, et.al.



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1-18-2010 CYCLE.PPT



INTRODUCTION

What are the advantages of reduced cycle time?

1. More responsive to changing customer demands. Especially important in ASIC (Application Specific Integrated Circuit) manufacturing.

2. Quicker time to market with new products.

3. Save money by reducing WIP (Work in progress)

4. Increase yield

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5. Quicker feedback for process development and process capability improvement programs. (Cpk will improve faster)

INTRODUCTION

What are the advantages of reduced cycle time? (Cont.)

6. Additional savings through incremental improvements:

6.1 Improved employee productivity, which means savings if less employees are needed or increased factory output if consistent with factory goals.

6.2 Improved equipment utilization by being smarter about maintenance, set ups, production tests, balance, etc.

6.3 Reduced non productive tests and process control measurements.

INTRODUCTION

What are some of the basic ways to improve cycle time? 1. Reduce WIP

1.1 Decrease input until WIP drops to desired value.

1.2 Increased line speed (the number of moves or turns per day) until WIP drops to desired value

- 1.2.1 adding labor
- **1.2.2 adding overtime**
- **1.2.3 reducing wasted time**
- 2. Reduce the number of process steps
- **3. Reduce the lot size.**

4. Reduce non value added operations. Like working on control wafers, measurements, unnecessary meetings, etc.5. Fine tuning.

All of the above needs to be done in such a way as to be consistent with output goals, factory tool capacity and direct labor goals for the factory.

DEFINITIONS

CYCLE TIME - the time it takes to process wafers from start to finish. Various cycle times can be calculated depending on the exact definition. Usually cycle time is the number of calendar days to process a lot from start to ship. Other variations include single wafer cycle times, cycle time based on work days rather than calendar, etc.

BASELINE CYCLE TIME (work days), (BSWCT and BWLCT) this is the cycle time at the start of a cycle time improvement program. At that point in time a CIM system data base query is done to find the cycle time for each process flow (PMOS, NMOS, CMOS, EEPROM, etc.) This is used as the reference point for measuring cycle time improvement.

DEFINITIONS

THEORETICAL SINGLE WAFER CYCLE TIME (TSWCT) the minimum cycle time calculated for a single wafer lot with no other wafers in the factory, no equipment down time, no queues, etc. (includes equipment set up time)

THEORETICAL WAFER LOT CYCLE TIME (TWLCT) - the minimum cycle time calculated for a single lot (typically 24 wafers but could be less) with no other wafers in the factory, no equipment down time, no queues, etc. Operations that one wafer at a time will result in additional processing time for the 2nd to Nth wafer in the lot. (includes equipment set up time)



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DEFINITIONS

ENTITLED CYCLE TIME (entitlement) - this is the goal for cycle time performance. It is somewhat arbitrary and is set low enough to be a challenge. For example the goal might be 2.5 X the TSWCT, which is considered world class today. In terms of wafer lot cycle time, one can calculate the ratio of TSWCT/TWLCT and that number times the single wafer goal is the equivalent wafer lot goal.

Example: if the TSWCT/TWLCT = 60% then 60% of 2.5 X = 1.5 X



DEFINITIONS

CYCLE TIME FOR A PARTICULAR LOT - any specific lot will have its own cycle time and as progress is made during the manufacture of the lot it may appear to be ahead or behind the average wafer lot cycle time.

Example: The RIT factory does a p-well CMOS process that has TWLCT of 200 hours. The process is 67 steps long. Each operator can do about 5 moves in an 8 hour day and we have a total of 10 operators each working 4 hours per week. Thus: 10 operators x 1/2 day/week x 5 moves/day = 25 moves per week

a) 67 steps/lot divided by 25 moves per week = 2.68 weeks @ 1X therefore at 3X it would take 8.0 weeks

b) 4 lots x 67 steps/lot divided by 25 moves per week = 10.7 weeks at 1X therefore at 3X it would take 32.1 weeks

c) a wafer lot started 3 weeks ago is at step 20 what is its X factor? It could be at step 75 so 75/20 = 3.75 X





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ASSESSMENT

THEORETICAL SINGLE WAFER AND WAFER LOT CYCLE TIMES

This is usually done by doing a factory data base query to find the minimum and average run times by operation. Then for each process the sum of the times for each operation in the process can give the cycle times. If the minimum times are used in the calculation the result is the theoretical wafer lot cycle time. The single wafer cycle times are calculated by subtracting the additional processing time for the 2nd to nth wafer (set up time is the same). The calculation using the minimum and the average values should be close. If they are not then same operation is taking different time depending on who is doing the operation. (at RIT this is often true, in industry this is less true)

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SUB-CMOS 150 PROCESS

SUB-CMOS Versions 150 1. ID01 -scribe 21. ET07 – Branson Asher 2. DE01 - 4pt probe 22. PH03 – 3 - p-well stop 3. CL01 – RCA Clean 23. IM01- stop B11 4. OX05--- pad oxide, Tube 4 24. ET07- Branson Asher 5. CV02- 1500 Å 25. CL01 – RCA Clean 6. PH03 –1- n well 26. OX04 – field. Tube 1 7. ET29 – LAM490 27. ET19 – Hot Phos 8. IM01 – n-well P31 28. ET06 – BOE 9. ET07 – Branson Asher 29. OX04 – Kooi, Tube 1 10. CL01 – RCA Clean 30. IM01 – Blanket Vt 11. OX04 - well oxide, Tube 1 31. PH03 - 4 - PMOS Vt Adjust 51. CV03 - TEOS, 5000A 12. ET19 – Hot Phos 32. IM01 – Vt- B11 13. IM01 – p-well B11 33. ET07 – Branson Asher 14. OX06 – well drive, Tube 1 34. ET06 - BOE 15. ET06 - BOE 35. CL01 – RCA Clean 16. CL01 – RCA Clean 36. OX06 - gate, Tube 4 17. OX05 – pad oxide, Tube 4 37. CV01 – Poly 5000A 18. CV02 - 3500 Å 38. IM01 - dope poly 39. OX08 – Anneal, Tube 3 19. PH03 – 2 - Active 20. ET29 – LAM 490 40. DE01 – 4pt probe

41. PH03 – 5 – poly 42. ET08 – LAM 490 43. ET07 – Branson Asher 44. PH03 – 6 - n-LDD 45. IM01 – LDD P31 46. ET07 – Branson Asher 47. PH03 – 7 - p-LDD 48. IM01 – LDD B11 49. ET07 – Branson Asher 50. CL01- RCA Clean 52. ET10 – Drytek Quad 53. PH03 – 8 - N+D/S 54. IM01 – N+D/S P31 55. ET07 – Branson Asher 56. PH03 – 9 P+ D/S 57. IM01 – P+ D/S B11 58. ET07 – Branson Asher 59. CL01 Special - No HF Dip 60. OX08 – DS Anneal, Tube 2,3

8-16-09

62. PH03 – 10 CC 63. ET06 - Drytek Quad / BOE 64. ET07 – Branson Asher 65. CL01 Special - Two HF Dips 66. ME01- CVC 601 67. PH03 -11- metal 68. ET15 – plasma Etch Al 69. ET07 – Solvent + Asher 70. SI01 – Sinter Tube 2 71. CV03 – TEOS- 5000Å 72. PH03 – VIA 73. ET06 - Drytek Quad / BOE 74. ET07- Strip Resist 75. ME01- PE 4400 76. PH03 - M2 77. ET15 -plasma Etch Al 78. ET07 – Solvent + Asher 79. SEM1 - pictures 80. TE01 81. TE02 82. TE03 83. TE04

61. CV03 – TEOS, 5000A



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ADV-CMOS 150 PROCESS

CMOS Versions 150, one level Metal 21. CL01 – RCA clean 41. IM01 – 4E13, B¹¹, 50 KeV 1. ID01 - scribe 61. RT02 - RTP 1 min.800C 2. DE01 - 4 pt probe 21.1 OX08 Anneal, Tube 1 42. ET07 – ash 62. CV03 – TEOS, P-5000 22. ET19 – hot phos – Si_3N_4 removal 43. PH03 – level 8 – n-LDD 3. CL01 – RCA clean 63. PH03 – level 11 - CC 4. OX05--- pad oxide 500 Å, Tube 4 23. OX06 well drive, 6hr 1100C, Tube1 44. IM01 – 4E13, P³¹, 60 KeV 64. ET06 – CC etch 5. CV02- 1500 Å Si₃N₄ Deposition 24. PH03 – level 4 – NMOS V_T adjust 45. ET07 – ash 65. ET07 – ash 25. IM01 – 2.15E12, P³¹, 60 KeV 46. CL01 – RCA clean 6. PH03 – level 1- STI 66. CL01 – RCA clean 7. ET29 - etch shallow trench, 4000 Å 26. ET07 – ash 47. CV02 – nitride spacer dep 67. ME01 – Aluminum 48. ET39 – sidewall spacer etch 68. PH03 – level 12-metal 8. ET07 – ash 27. PH03 – level 5 – PMOS V_T adjust 9. CL01 – RCA clean 28. IM01 – 1.75E12, B¹¹, 60 KeV 49. PH03 - level 9 - N+D/S 69. ET15 – plasma Al Etch 10. OX05 – liner oxide, 500 Å, Tube 4 29. ET07 – ash 50. IM01 – 4E15, P³¹, 60 KeV 70. ET07 – ash 30. ET06 – etch 500 Å pad oxide 51. ET07 – ash 11. PH03 – level 2 - n-well 71. SI01 – sinter 31. CL01 – pre-gate oxide RCA clean 52. PH03 – level 10 - P+ D/S 12. IM01 – 3E13, P³¹, 170 KeV 72. SEM1 32. ET06 – etch native oxide 13. ET07 – ash 53. IM01 – 4E15, B¹¹, 50 KeV 73. TE01 33. OX06 – 100 Å gate oxide, Tube 4 54. ET07 – ash 14. PH03 – level 3 – p-well 74. TE02 34. CV01 – poly deposition, 4000 Å 15. IM01 – 8E13, B¹¹, 80 KeV 55. CL01 – RCA clean 75. TE03 56. OX08 – DS Anneal, Tube2,3 76. TE04 16. ET07 – ash 35. PH03 – level 6 – poly gate 36. ET08 – poly gate plasma etch 57. ET06 – Silicide pad ox etch 17. CL01 – RCA clean $L = 0.5 \,\mu m$ 18. CV03 – oxide trench fill, P-5000 37. ET07 – ash 58. ME03 – HF dip & Ti Sputter $V_{DD} = 3.0 V$ 19. CM01 – Trench CMP 38. CL01 – RCA clean 59. RT01 – RTP 1 min, 650C 39. OX05 – poly re-ox, 500 Å, Tube 4 60. ET11 – Unreacted Ti Etch $V_{TN} = 0.75 V$ 20. CL02 - CMP Clean 40. PH03 - level 7 - p-LDD $V_{TP} = -0.75V$



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(Revision 1-6-09)



	CL01			CV01			CV02	
AVE		64	AVE		203	AVE		171
MIN		20	MIN		120	MIN		20
MAX		200	MAX		301	MAX		480
COUNT	181		COUNT	26		COUNT	25	
	CV03			DE01			DI01	
AVE		226	AVE		27	AVE		170
MIN		60	MIN		11	MIN		60
MAX		999	MAX		100	MAX		360
COUNT	25		COUNT	48		COUNT	22	
	DI02			DI04			ET01	
AVE		39	AVE		110	AVE		170
MIN		10	MIN		15	MIN		60
MAX		180	MAX		230	MAX		360
COUNT	235		COUNT	27		COUNT	22	
	ET02			ET07			ET08	
AVE		58	AVE		53	AVE		103
MIN		20	MIN		15	MIN		30
MAX		140	MAX		180	MAX		180
COUNT	264		COUNT	24		COUNT	24	
						1		
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	ЕТ09			GR01			ID01	
AVE		101	AVE		25	AVE		23
MIN		20	MIN		20	MIN		13
MAX		240	MAX		30	MAX		45
COUNT	49		COUNT	18		COUNT	10	
	IM01			ME01			OX01	
AVE		113	AVE		173	AVE		170
MIN		12	MIN		30	MIN		60
MAX		700	MAX		300	MAX		360
COUNT	261		COUNT	22		COUNT	22	
	OX02			OX03			OX04	
AVE		39	AVE		196	AVE		211
MIN		10	MIN		30	MIN		55
MAX		180	MAX		360	MAX		720
COUNT	235		COUNT	18		COUNT	78	
	OX05			OX06			OX07	
AVE		163	AVE		178	AVE		170
MIN		60	MIN		20	MIN		60
MAX		360	MAX		999	MAX		360
COUNT	20		COUNT	55		COUNT	22	
			I			1		
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	Microelectron	ic Engineering						

				PH03			5101	
AVE		113	AVE		116	AVE		170
MIN		45	MIN		15	MIN		60
MAX		180	MAX		360	MAX		360
COUNT	19		COUNT	221		COUNT	22	
	TE01			TE02			TE03	
AVE		133	AVE		126	AVE		117
MIN		60	MIN		60	MIN		45
MAX		240	MAX		180	MAX		180
COUNT	17		COUNT	16		COUNT	16	
	TE04		IM01 SH	ETUP			TOTAL	
AVE		110	AVE		49	AVE		100
MIN		60	MIN		0	MIN		11
MAX		180	MAX		180	MAX		999
COUNT	6		COUNT	261		COUNT	1,567	
FP								
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	Microelectron	ic Engineering						

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Microelectro	nic Engineeri	ng				Name: asse	ss.xls	
Microelectro	nics Manufac	turing						
	FROM DATA	ABASE	CMOS-PW3	Process				
					((C-B)/E+B)*C	C*D*E		
Operation	Ave Lot	minimum	Process	Lot	Theoretical	Theoretical		
	Setup time	lot run time	Operation	Multiplier	Single Wafer	Wafer Lot		
			Repeats		Cycle Time	Cycle Time		
	minutes	minutes			minutes	minutes		
ID01	0	10	1	3	3.3	30.0		
DE01	0	15	2	1	30.0	30.0		
CL01	15	45	9	1	405.0	405.0		
OX05	60	180	2	1	360.0	360.0		
CV02	60	150	1	1	150.0	150.0		
PHO3	30	120	9	3	540.0	3240.0		
ETO9	30	60	2	3	80.0	360.0		
ET06	0	10	4	3	13.3	120.0		
IMO1	60	90	6	3	420.0	1620.0		
ET07	0	45	9	1	405.0	405.0		
OX04	60	180	2	1	360.0	360.0		
GR01	0	30	0	1	0.0	0.0		
ET03	0	10	1	1	10.0	10.0		
0X06	60	120	2	1	240.0	240.0		
CV01	60	90	1	1	90.0	90.0		
DI04	60	180	1	1	180.0	180.0		
ET02	0	10	1	1	10.0	10.0		
ET08	60	60	1	3	60.0	180.0		
CV03	60	90	1	1	90.0	90.0		
ME01	120	180	1	1	180.0	180.0		
SI01	60	60	1	1	60.0	60.0		
ET05	60	90	1	1	90.0	90.0		
TE01	0	60	4	1	240.0	240.0		
TOTALS=			62		4016.7	8450.0	minutes	
					8.4	17.6	days	

ASSESSMENT

GOAL or ENTITLED CYCLE TIME (entitlement) - this is the goal for cycle time performance. It is somewhat arbitrary and is set low enough to be a challenge. For example the goal might be 2.5 X the TSWCT, which is considered world class today. In terms of wafer lot cycle time, one can calculate the ratio of TSWCT/TWLCT and that number times the single wafer goal is the equivalent wafer lot goal.

Example: if the TSWCT/TWLCT = 60% then 60% of 2.5 X = 1.5 X

Thus 2.5 X TSWCT is equivalent to 1.5 X TWLCT



ASSESSMENT

BASELINE SINGLE WAFER AND WAFER LOT CYCLE TIMES

A data base query is made to determine the date lots were started and the date they were completed. The difference is the Cycle Time in Calendar Days.

A data base query is made to determine the number of work days between the start of a lot and the completion of a lot. This is the Cycle Time in Work Days.



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		Cycle Time Ma	anagement			
		ASSESS	MENT			
DAY	DATE	LOT NUMBER	R PRODUCT	STEP	FROM	TO
2,956	98-02-16	F970620	RIT-FAC-CPW	V- 0944	59	60
2,727	97-04-14				1	2
2,915	98-01-05	F970414	RIT-FAC-CPW	V-2000	58	59
2,654	97-04-14				1	2
2,918	98-01-08	F970324	RIT-FAC-CPW	V- 0944	59	60
2,634					1	2
ETC.						

SUBTRACT DAY FOR STEP 1 FROM DAYS FOR LAST STEP TO GET CYCLE TIME IN CALENDAR DAYS

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OUFRV NAM	F•CVCI FT	'IMF?		I IRRARV•MFSADI			
FILE: LTLMI	D101		FORMAT:LTFMD101				
RESULT FIEI	LDS:	DATE					
MDT	TRYR*10,00	0+MDTRMO*100-	+MDTRE	ΟY			
	DAYS	(MDTRYR-90)*1	12*30+M	DTRMO*30+MDTRD			
SELECT REC	CORDS:	DATE	GT	950101			
	AND	MDLOT LIKE	'F%'				
	AND	MDMVTP	EQ	'1'			
	AND	MDPRDI	LIKE	'%FAC%'			

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ASSESSMENT

This Query gives the date for any day that a factory move was made. This is combined with the start date and end date from the CYCLETIME1 query results to give the Cycle Time in work days.

		I		1			1		
	Date		Date		Date		Date		Date
	97-04-24		97-04-14		97-04-28		97-05-02		
COUNT	10	COUNT	2	COUNT	5	COUNT	4	COUNT	
	97-04-04		97-04-17		97-04-30		97-06-03		
COUNT	3	COUNT	9	COUNT	3	COUNT	2	COUNT	
	97-04-06		97-04-20		97-05-04		97-06-04		
COUNT	1	COUNT	1	COUNT	1	COUNT	7	COUNT	
	97-04-07		97-04-21		97-05-05		97-06-05		
COUNT	5	COUNT	6	COUNT	7	COUNT	1	COUNT	
	97-04-09		97-04-22		97-05-07		97-06-08		
COUNT	5	COUNT	2	COUNT	2	COUNT	2	COUNT	
	97-04-10		97-04-23		97-05-27		97-06-09		
COUNT	8	COUNT	4	COUNT	2	COUNT	3	COUNT	
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ASSESSMENT

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MICROELE	ECTRONIC	ENGINEER	RING						
CYCLE TIN	ЛЕ								
			WORK	CALENDAR					
END	START	LOT #	DAYS	DAYS	PROCESS	TSWCT	X-FACTOR	2	
1/6/97	4/3/96	F960401	123	283	CMOS-4	10	12		
2/11/97	5/2/96	F96001	139	279	CMOS-3	8	17		
9/4/96	5/2/96	F960502	61	122	CMOS-4	10	6		
1/17/97	9/9/96	F960909	64	128	CMOS-3	8	8		
3/17/97	9/30/96	F960930	83	167	CMOS-4	10	8		
7/2/97	10/28/96	F961028	122	244	CMOS-4	10	12		
9/17/97	12/3/96	F961203	142	284	CMOS-3	8	18		
7/16/93	7/13/93	L930712	4	4	PMOS	2	2		
9/29/93	9/6/93	L930906	9	24	PMOS	2	5		
2/17/97	12/12/96	F961212	33	65	NWELL	4	8		
9/15/97	1/10/97	F970110	123	245	CMOS-3	8	15		

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CYCLE TIME REDUCTION

Combining the equations above we see an expression for Cycle Time that includes WIP, Starts, turns, Turns/start, and Yield.

Cycle Time =
$$\frac{2 (WIP) (T)}{t (1 + Y)}$$

It becomes obvious from the above equations that to decrease cycle time one should

```
decrease WIP and/or Turns/Start (T)
```

and/or

increase Yield and/or turns (t)

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CYCLE TIME REDUCTION

WIP reduction is normally achieved by setting the starts to a number somewhat lower than the sum of Outs plus scrap. Then over a period of months (6 to 12 months) the WIP is gradually reduced to a predetermined level.

Line speed is increased by increasing the daily turns, t, simplifying the process to reduce the number of steps in the process (T) turns/start, and/or increasing the process yield (Y)

To increase the daily turns one could use overtime, add labor, and/or increase productivity. This activity must be combined with proper control of wafer input to control WIP otherwise increasing the daily turns may not result in a decrease in cycle time.



CYCLE TIME REDUCTION

"Caution!!! Most fabs will first choose to focus exclusively on increasing turns and not set starts at a level consistent with turns capability and a plan to reduce WIP. The reason is probably because the fab is being driven harder than its existing capability and still not meeting demand. Any mention of a reduction in starts is met with strong opposition. The belief is that a push for more turns is always possible. It is a fatal mistake to not regulate starts as part of the plan to reduce WIP. You simply can not "outrun" the starts. To increase turns, especially if overtime is used up is not easy and if it an be done at all it takes time. Hiring and training more people also takes time. A successful cycle time reduction plan must plan to increase turns and plan to regulate starts in such a way as to systematically reduce the WIP over a period of time". Jack Scholl, Motorola





2. Calculate the daily outs by using the weighted required turns/start, the process yield of the line and the daily turns.

3. Determine the final desired WIP goal and when this is to be achieved. Divide the delta in WIP by the number of weeks to get an average delta inventory per week. (Typical numbers might be to drop 1000 wafers per month which works out to about 50 wafers per day.)

4. Set daily inputs at a level 50 wafers below the sum of daily Outs plus daily scrap.

CYCLE TIME REDUCTION

Over the following months, if the plan is a good one, the inventory should drop without any drop in the output of the line. Even though the starts have been lowered, the output is maintained as the dropping WIP continues to drive the outs. It is very important during this time to carefully monitor two critical parameters: daily turns and daily turns/WIP. An increase in the daily turns/WIP is an indication that the cycle time is improving, but it is important that this be achieved without reducing turns which would cause outs to be missed. As the WIP is reduced sooner or later the factory will begin to struggle to maintain the daily turns due to reduced buffer stock not being available when equipment or processes go down. When this happens it is time to re-evaluate the WIP reduction plan.



CYCLE TIME REDUCTION

Caution!!! Although a good WIP control program will definitely produce an improvement in cycle time, it is primarily aimed at targeting starts at a level consistent with the factory's demonstrated ability to turn product. Continuing to reduce WIP beyond the point where turns begin to drop may make a good looking cycle time graph, but it will also reduce output which can result in a dramatic negative impact to business." Jack Scholl, Motorola



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CYCLE TIME REDUCTION

Example: Given a factory that typically does 30,000 turns/day and the number of wafers started per week is 5000. If the number of turns per start is 50 calculate the change in WIP after one week.

5000 wafers x 50 turns/wafer = 250,000 turns and the number of turns per week is $30,000 \ge 7 = 210,000$ so WIP will increase by 40,000 turns or about 800 wafers. After 1 month that will be 3200 wafers and after four months WIP will increase by 12,800 wafers and increasing every month.

This factory is not balanced and it will be necessary to decrease input or increase turns. Turns is directly related to output and if the customer demand exists it is useful to look at increasing turns.



CYCLE TIME REDUCTION

Increasing turns (Line Speed) can be done by adding labor or by improving the efficiency of the labor already employed. The people working in the factory spend some of their time in productive activities and some in non-productive activities. Some of the non-productive activities are required. The goal should be to minimize the required nonproductive activities and maximize the productive activities of labor.



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CYCLE TIME REDUCTION

PRODUCTIVE HOURS (MAXIMIZE) Processing Wafers

NON-PRODUCTIVE HOURS (MINIMIZE) REQUIRED (MINIMIZE)

Department Meetings Team Improvement Activities Vacation/Sick Time Essential Set-up and Monitors Training Clerical/Administrative Duties

NOT REQUIRED (ELIMINATE)

No Equipment Process/Equipment Down Excessive Equipment Set-up Excessive Qualifications Equipment Modifications No Material Out of Balance Line Material on Hold Minimum Load Sizes No Operator Absenteeism Excessive Paperwork Start-up/shut down Idle time

CYCLE TIME REDUCTION

Example: The figure on the next page illustrates the relationship between turns, WIP and cycle time. The data represents a factory at three different times (Time-1, Time-2, and Time-3) in its cycle time improvement program where the turns per day is given by T1, T2, and T3 and the corresponding cycle time is C1, C2 and C3.

Initially at Time-1 the factory is capable of a maximum of 30K turns per day unless the WIP drops below 20K wafers then lower WIP would result in lower turns per day. This is point "A" the cycle time is 23 days.

At a later Time-2 the factory is generating up to 35K turns per day. The factory can either reduce cycle time or increase capacity.





CYCLE TIME REDUCTION

At Time-1:

At point A the WIP is 20K wafers, Cycle Time is 23 days, Turns are 30K At Time-2:

At point B1 the WIP is 23K wafers, Cycle Time is 23 days, Turns are 35K At point B2 the WIP is 20K wafers, Cycle Time is 22 days, Turns are 32K At point B3 the WIP is 18K wafers, Cycle Time is 21 days, Turns are 30K

At Time-2 lets say that the factory has increased the turns capability to 35K turns per day. A decision could be made to use the possible increase in turns/day to increase factory output (B1) and not reduce Cycle Time, or to reduce Cycle Time a little compared to Time-1 while increasing the output a little to 32K turns/day (B2), or to keep the output the same at 30K turns/day and decrease cycle time to 21 days.



SPLIT THE WIP

If the current cycle time is less than 3 times theoretical than an action plan to gradually decrease WIP over a period of six months to a year, with an objective of cutting the cycle time in half should be considered. For fabs with time greater than 3.5 times theoretical a technique called "split-the-WIP" should be considered.



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C<mark>ycle Time Management</mark>

SPLIT THE WIP

1. Analyze the WIP - looking for the high volume products. Normally 80% of the WIP is associated with only 20% of the products. We would like to select products that have more than several lot starts per week called high volume. Working with the high volume products identify about half of that WIP to be split. The low volume WIP will be given no special treatment.

2. Remove one half of all lots between the first step and first layer metal (almost last step). These lots are put on hold at the next safe point (generally just prior to the next photo step, that is no abnormally exposed silicon) and actually removed from the factory. At this time wafer starts on these products (the major products) are discontinued.

3. Starts are continued as normal on low volume products. No new starts are made on high volume products.

4. When the lots which were at the first step reach first metal photo, we will move all of the lots which were on hold back into the fab. At this point starts on all products are resumed as normal.

SPLIT THE WIP

Example: Fab Prior to Split-the-WIP

Total WIP Wafers on Hold Total Weekly Starts Starts for High volume Products Starts for Remainder WIP of High Volume Products WIP of Remainder Daily Turns (moves) Turns-to-WIP Ratio Wafer Ships to Probe @95% yield

25,000 wafers
0 wafers
5,000 wafers
2,500 wafers
2,500 wafers
12,500 wafers
12,500 wafers
30,000 wafers
1.2
4,750 wafers/week

SPLIT THE WIP

Example: Fab Immediately Following Start of WIP Split

Total WIP18Wafers on Hold6,7Total Weekly Starts2,7Starts for High volume Products0Starts for Remainder2,7WIP of High Volume Products6,7WIP of Remainder12Daily Turns (moves)30Turns-to-WIP Ratio1.4Wafer Ships to Probe @95% yield4,7

18,750 wafers
6,250 wafers
2,500 wafers
0 wafers
2,500 wafers
6,250 wafers
12,500 wafers
30,000 wafers
1.6
4,750 wafers/week

C<mark>ycle Time Management</mark>

SPLIT THE WIP

During the period of Split-the-WIP (about 2 to 2.5 weeks), no starts are made on the high volume products involved in Split-the-WIP. The fab is run normally during this period. However, we must keep tabs on the high volume products which are in the fab. When the lots which were at the first step reach metal photo, we will move all of the lots which were on hold back into the fab.

Example: Fab just prior to bringing in the wafers that were on hold

Total WIP12,500Wafers on Hold6,250Total Weekly Starts2,500Starts for High volume Products0Starts for Remainder2,500WIP of High Volume Products0WIP of Remainder12,500Daily Turns (moves)30,000Turns-to-WIP Ratio2.4Wafer Ships to Probe @95% yield4,750

12,500 wafers
6,250 wafers
2,500 wafers
0 wafers
2,500 wafers
2,500 wafers
12,500 wafers
30,000 wafers
2.4
4,750 wafers/week



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SPLIT THE WIP

Example: Fab at Completion of Split-the-W	/IP
Total WIP	18,750 wafers
Wafers on Hold	0 wafers
Total Weekly Starts	5,000 wafers
Starts for High volume Products	2,500 wafers
Starts for Remainder	2,500 wafers
WIP of High Volume Products	6,250 wafers
WIP of Remainder	12,500 wafers
Daily Turns (moves)	30,000 wafers
Turns-to-WIP Ratio	1.6
Wafer Ships to Probe @95% yield	4,750 wafers/week

Note: the wafers shipped to probe was constant in all of the above examples.

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RAMP UP

Ramp up refers to the process of increasing output from a semiconductor fab.

"Often the process was to increase input and wait for one cycle time, then look for the increase in output. What would really happen would be an increase in WIP and an increase in cycle time with no increase in output" Tom Filesi, Motorola.

In order to increase output labor needs to be increased either through more people or overtime so that more turns will be generated each day.





	Cycle Time Management	
	RAMP UP	
Examp	ole:	
Given increas	the average turns per start is 60, lets say we want an se in 20 wafer outs per day.	
Then 6 turns/v	50 turns/wafer x 20 wafers/day x 5 days/week = 6000 week	
6000 tu overtir	urns/week divided by 15 turns/hour = 400 hours/week of ne or 10 additional people	
This is capacit	a simplistic approach that does not include machine ty and other considerations.	
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MACRO PLANNING

A simple approach to macro planning is described below. It is basically a spreadsheet model of a factory operation that emphasizes cycle time. The model takes into consideration a variety of details associated with the factory including:

> process yield number of operators attendance work schedule scrap rate bottlenecks multiple processes tool uptime tool capacity rework

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MACRO PLANNING

See Spreadsheet CYCLE2MOD.XLS See Tools Folder on your CD

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OPER	TOOL	RAW	UP time	REWORK	PLAN	PLAN	NEED	Bottleneck						
NAME		W/H	%	%	W/H	W/WK	W/WK	STATUS						
									0.0 t	0	0.25	0	.50	0.75
ID01	SCRIBE	40	90	5	34	4104	53	0.01	1	l				
PHOTO	STEPPER	10	80	5	8	912	547	0.60						
	TRACK	20	80	5	15	1824	547	0.30				l		
CL01	CLEAN	60	99	0	59	7128	547	0.08	4					
IMP MED		20	80	5	15	1824	158	0.09	1					
IMP HIGH		1	90	1	1	107	84	0.79						
RIE	Poly	4	90	0	4	432	42	0.10	7					
	Nitride	4	90	0	4	432	84	0.19						
	CC	4	90	5	3	410	42	0.10						
OXIDE	Gate	100	90	5	86	10260	11	0.00	10					
	Drive	100	90	5	86	10260	53	0.01						
	Anneal	100	90	5	86	10260	53	0.01						
	Kooi	100	80	5	76	9120	53	0.01	13					
	Pad	100	90	5	86	10260	42	0.00	1					
	5000 Wet	50	90	5	43	5130	42	0.01						
DIFF	POLY	20	90	5	17	2052	63	0.03	16					
	D/S	20	90	5	17	2052	32	0.02		1				
CVD NITR	Nitride	1	90	5	1	103	11	0.10						
	Poly	1	85	5	1	97	84	0.87	19					
	Oxide	1	85	5	1	97	42	0.43						
METAL		10	85	5	8	969	42	0.04						
ETCH	Oxide	100	90	5	86	10260	53	0.01	22					
	Metal	25	95	5	23	2708	242	0.09						
STRIP		75	95	5	68	8123	53	0.01						
GROOVE		25	90	5	21	2565	547	0.21	25					
4PT PROE	3E	100	95	5	90	10830	32	0.00	[
TEST		3	100	0	3	360	126	0.35						
SHIP		100	100	0	100	12000	158	0.01	28			_		



HOMEWORK - CYCLE TIME

- 1. Discuss five reasons why reducing cycle time is good.
- 2. What can be done to reduce cycle time?
- **3.** Derive the equation for cycle time shown below

Cycle Time =
$$\frac{2 (WIP) (T)}{t (1 + Y)}$$

4. Give an example of split-the-wip (not the same as in the notes).

5. Using a spread sheet model similar to that shown in CYCLE2MOD.XLS investigate setting up a factory for 5000 wafers per week.

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